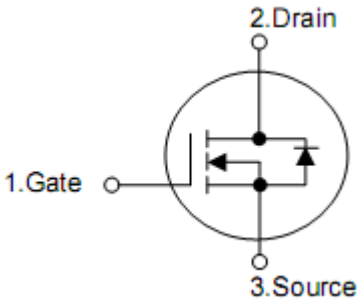
1. Features

- Advanced SGT technology
- $R_{DS(ON)}$=1.5mΩ (typ.) @ V_{GS}=10V
- Super Low Gate Charge
- Green Device Available
- Excellent CdV/dt effect decline
- 100% ΔVds TESTED
- 100% UIS TESTED

2. Pin configuration

DFN5*6



Pin	Function
4	Gate
5,6,7,8	Drain
1,2,3	Source

3. Ordering Information

Part Number	Package	Brand
KCY2704B	DFN5*6	KIA

4. Absolute maximum ratings

T_C=25°C unless otherwise specified

Parameter		Symbol	Ratings	Unit
Drain-to-Source Voltage (V_{GS}=0V）		V_{DS}	40	V
Gate-to-Source Voltage (V_{DS}=0V）		V_{GS}	±20	V
Continuous Drain Current [1]	T_C=25°C	I_D	160	A
	T_C=100°C	I_D	110	A
Pulsed Drain Current @ Current-Pulsed [2]		I_{DM}	640	A
Total Power Dissipation (T_C=25°C) [4]		P_D	111.1	W
Avalanche Energy [3]		EAS	441	mJ
Operation Junction and Storage Temperature Range		T_J,T_{STG}	-55 to 150	°C

5. Thermal characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case [1]	$R_{\theta JC}$	1.35	°C/W

6. Electrical characteristics

(T_A=25°C, unless otherwise notes)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250uA	40	-	-	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=40V,V_{GS}=0V, T_C=25°C	-	-	1	uA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=-250uA	1.0	1.5	2.5	V
Static Drain-Source On-Resistance 2)	$R_{DS(ON)}$	V_{GS}=10V, I_D=30A	-	1.5	1.8	mΩ
		V_{GS}=4.5V, I_D=20A	-	2.0	2.6	mΩ
Gate Resistance	R_g	V_{DS}=0V, V_{GS}=0V,f=1.0MHz	-	2.0	-	Ω
Input Capacitance	C_{iss}	V_{DS}=20V , V_{GS}=0V , f=1.0MHz	-	3250	-	pF
Output Capacitance	C_{oss}		-	1570	-	pF
Reverse Transfer Capacitance	C_{rss}		-	60	-	pF
Turn-On Delay Time	$T_{d(on)}$	V_{DS}=20V,V_{GS}=10V, R_G=2.0Ω,I_D=30A	-	17	-	ns
Rise Time	T_r		-	9	-	ns
Turn-Off DelayTime	$T_{d(off)}$		-	58	-	ns
Fall Time	T_f		-	30	-	ns
TotalGate Charge	Q_g	V_{DS}=20V, V_{GS}=10V , I_D=30A	-	63	-	nC
Gate-Source Charge	Q_{gs}		-	8.5	-	nC
Gate-Drain Charge	Q_{gd}		-	10	-	nC
Source-Drain Current (Body Diode) 1),5)	I_{SD}	—	-	-	160	A
Diode Forward Voltage 2)	V_{SD}	V_{GS}=0V, I_{SD}=30A,T_J=25°C	-	-	1.2	V
Reverse Recovery Time	t_{rr}	T_J=25°C, I_F=30A, di/dt=100A/μs	-	53	-	nS
Reverse Recovery Charge	Q_{rr}		-	70	-	nC
Forward Turn-on Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS +LD)				

Notes:
1) The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2) The data tested by pulsed, pulse width≤300us, duty cycle≤2%.
3) The test condition is V_{DD}=24V, V_{GS}=10V, L=0.5mH, I_{AS}=42A.
4) The power dissipation is limited by 175°C junction temperature.
5) The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

7. Typical Characteristics

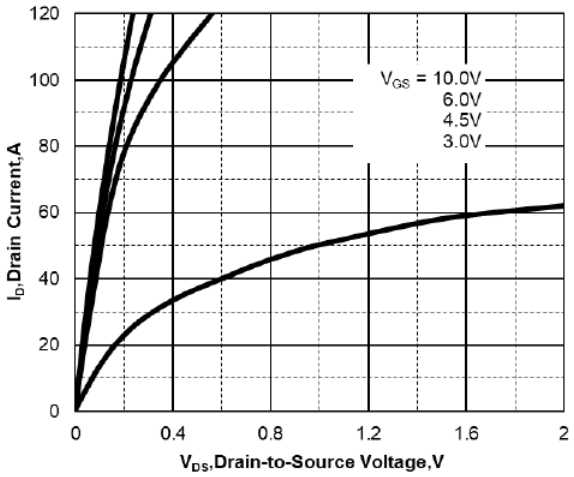


Fig1: Typical Output Characteristics

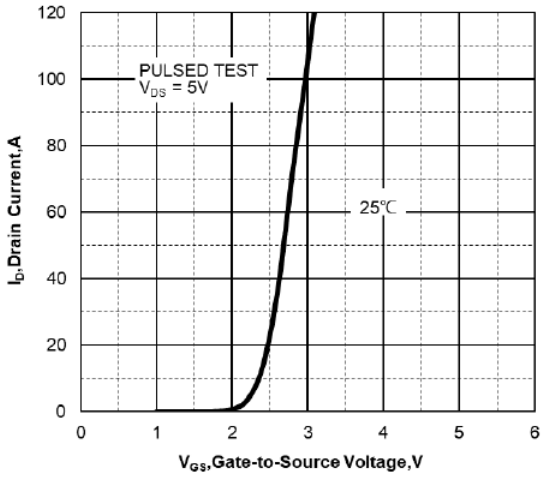


Fig 2: Typical Transfer Characteristics

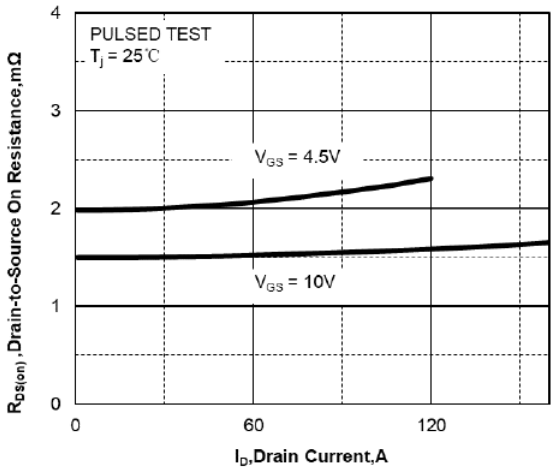


Fig 3: On-Resistance VS. Drain Current

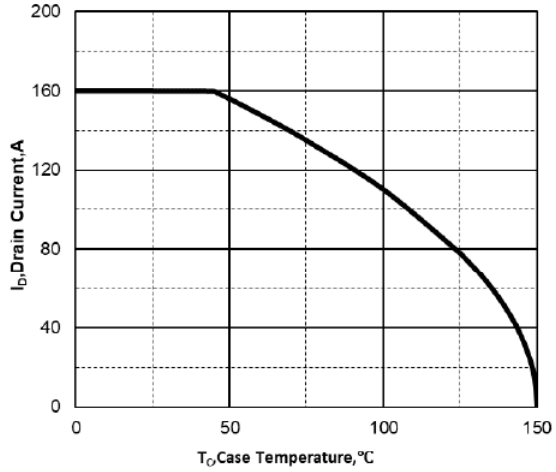


Fig 4: Maximum Continuous Drain Current VS. Case Temperature

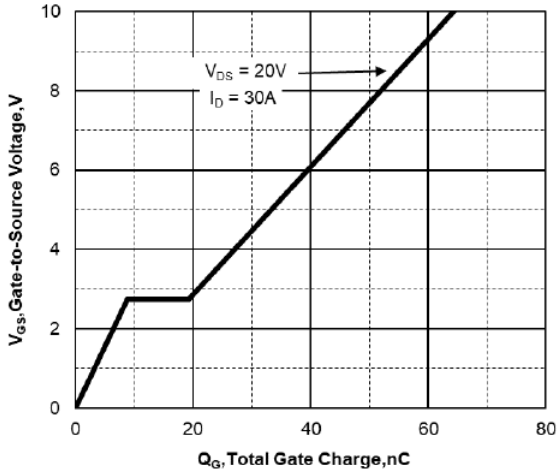


Fig 5: Gate Charge Characteristics

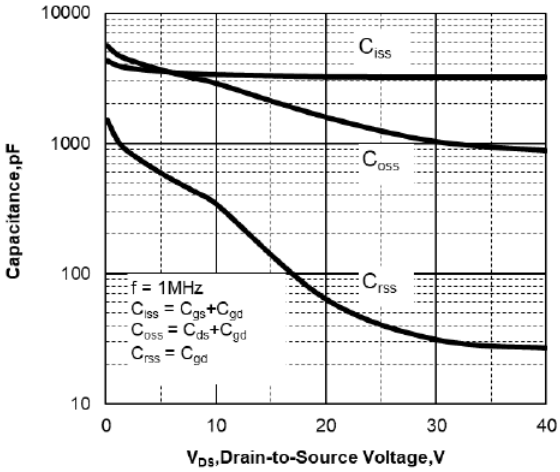


Fig 6: Capacitance Characteristics

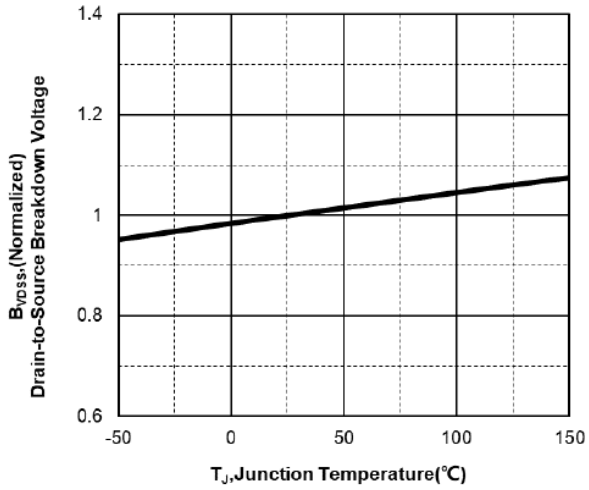


Fig 7: Normalized Breakdown Voltage VS. Junction Temperature

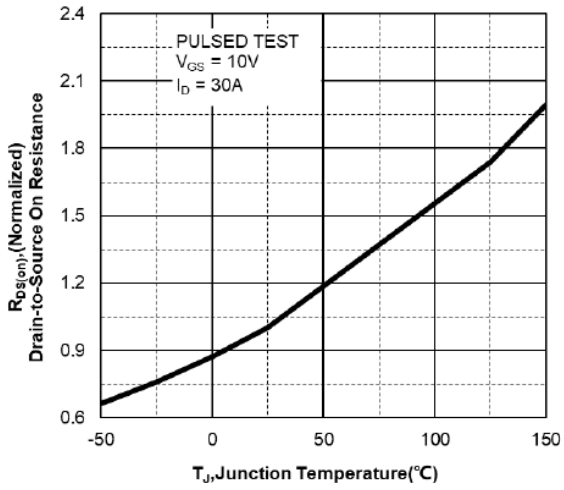


Fig 8: Normalized on Resistance VS. Junction Temperature

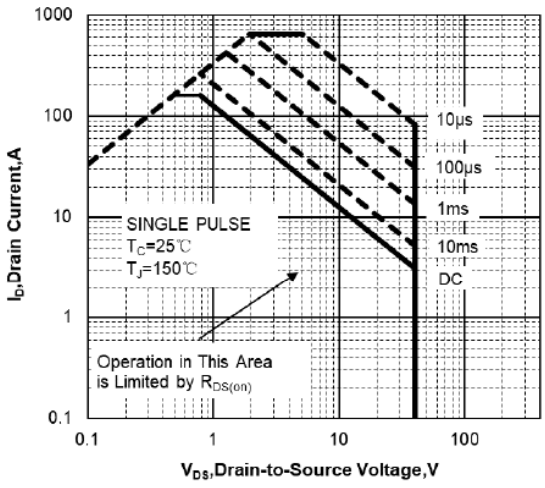


Fig 9: Maximum Safe Operating Area

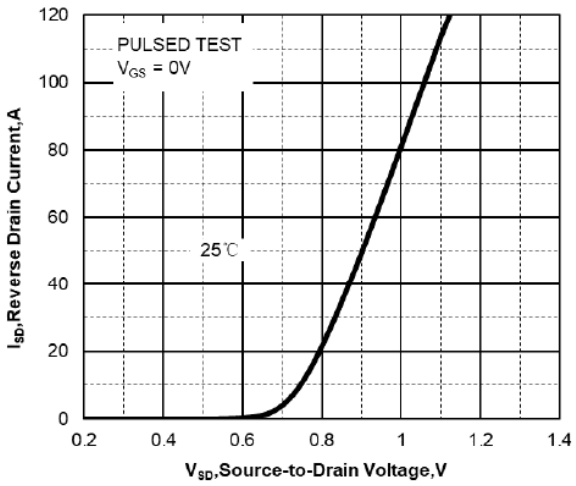


Fig 10: Body Diode Forward Characteristics

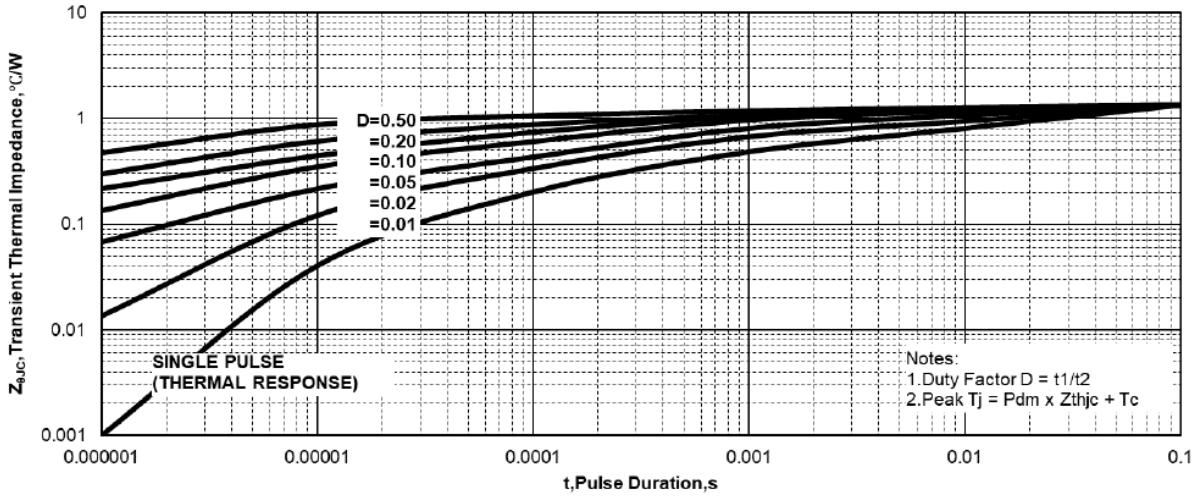


Fig.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

8. Test Circuit & Waveform

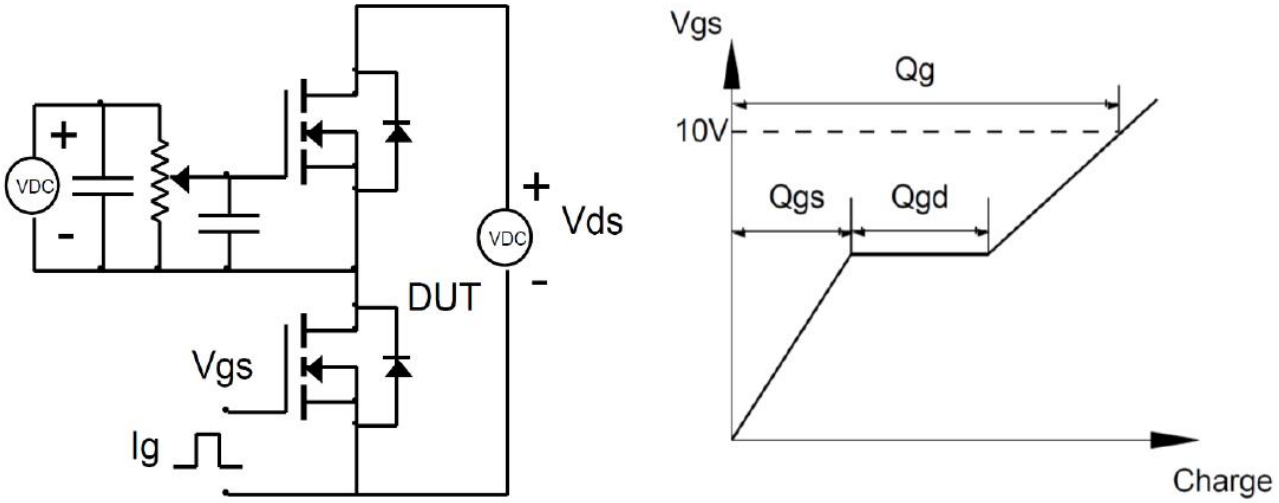


Fig 12: Gate Charge Test Circuit and Waveforms

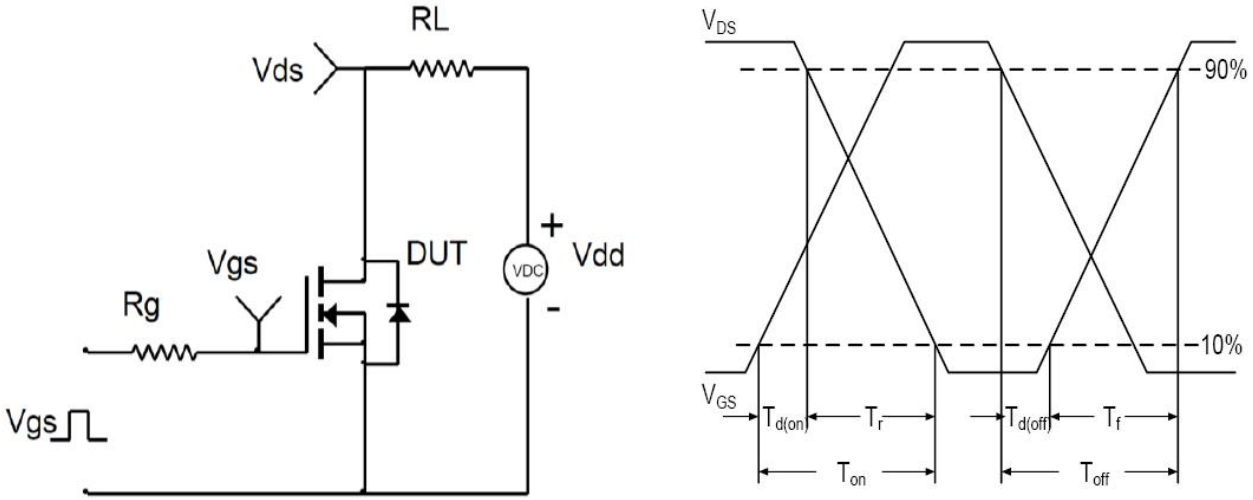


Fig 13: Resistive Switching Test Circuit and Waveforms

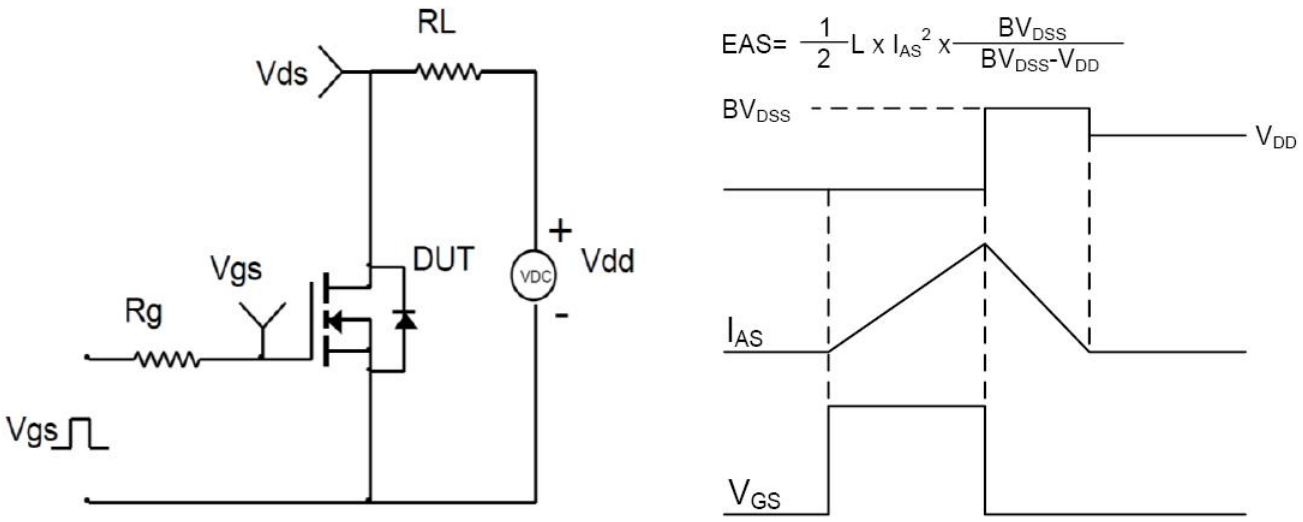


Fig 14: Unclamped Inductive Switching Test Circuit and Waveforms